IS. El mov<sup>1</sup>, T. Saha-Dasgupta<sup>2</sup> and M A. Korotin<sup>3</sup>
<sup>1</sup>Department of Physics and Astronomy, University of British Columbia, 6224 Agricultural Road, Vancouver, B.C. V 6T 1Z1, Canada
<sup>2</sup>S.N. Bose. National Center for Basic Sciences JD Block, Salt Lake, Kolkata 700 098, India
<sup>3</sup>Institute of M etal Physics, 620219 Ekaterinburg G SP-170, Russia

The common interpretation of the LDA band structure of V<sub>2</sub>O<sub>3</sub> is that the apparent splitting of the  $a_{1g}$  band into a low intensity structure deep below the Ferm intensity and a high intensity feature above it, is due to the bonding-antibonding coupling of the vertical V-V pair. U sing tight-binding tting to {as well as rst-principles NM TO downfolding of{ the spin-up LDA + U  $a_{J}$  band, we show that there are other hopping integrals which are equally in portant for the band shape as the integral for hopping between the partners of the pair.

A few years ago, Park et al. reexam ined the socalled spin 1/2 model for  $V_2O_3$  [1]. Based on polarization dependent x-ray absorption m easurem ents they showed that, for all phases, the vanadium 3+ ion  $(d^2)$  is in the spin 1 state. They also dem onstrated that this state is a mixture of  $e_{\alpha}e_{\alpha}$  and  $e_{\alpha}a_{1g}$  congurations, with the form er having the larger weight, especially at low tem peratures. Recall, that the  $t_{2q}$  orbitals, which are pd anti-bonding with the 0 p orbitals on the surrounding octahedron, lie below the pd anti-bonding eq orbitals and are split by a trigonal distortion into low -lying, doubly degenerate  $e_{\alpha}$  orbitals and a higher-lying  $a_{1\alpha}$  orbital. The picture presented by Park et al. is hardly consistent with the classical vertical-pair assumption that the bonding-antibonding splitting of the  $a_{1g}$  orbitals of the V-V pair places the energy of the bonding orbital well below that of the  $e_{\alpha}$  orbitals [2, 3]. This is the assum ption which 25 years ago led Castellani et al. to suggest the spin 1/2 m odel where for the V-V pair two electrons

ll the bonding  $a_g$  orbital and the two remaining electrons 1/4- ll the four g orbitals [4]. It is now generally recognized that the spin 1/2 model is incorrect. Nevertheless, the vertical pair remains a popular starting point for current attempts to calculate the electronic structure of V<sub>2</sub>O<sub>3</sub> [5, 6, 7]. A comprehensive review of the latest experimental and theoretical results in this eld can be found in a recent paper by D iM atteo, Perkins and N atoli [8].

In the present paper we study the dispersion of the  $a_{1g}$  band obtained from a modern LDA + U calculation by performing a tight-binding analysis. Our motivation for doing this is to obtain information regarding the smallest cluster that one can use in the model calculations while still preserving the most important aspects of the band structure. In spite of the fact that some literature exists providing the qualitative hint concerning this, we considered it to be rather important to check this with more recent methodology (e.g. the downfolding tech-

nique) providing the quantitative estimates. Note that, although the spatial orientation of an  $a_{1g}$  orbital is actually in favour of a molecular-like picture, our analysis shows that there are other hopping integrals which are equally in portant for description of the main features of the band structure as the hopping integral between the partners of the caxis pair ( $t_1$ ). Though these inter-pair hopping integrals are smaller than  $t_1$ , the contribution is proportional to the num ber of neighbours and that makes them rather signi cant.

Since we are interested in understanding the relative in portance of the hopping between pairs and non-pairs, we consider the band structure of ferrom agnetic  $V_2O_3$ in the high-temperature corundum structure. A lthough this phase does not exist in nature, it can provide a good estimate of an upper bound for the hopping integrals in this compound for the following reasons: First of all, comparing with antiferrom agnetic phases, the ferrom agnetic one has the largest band-width [10]. Secondly, the distance between the partners of a vertical pair is shorter in the corundum structure than in the low-temperature monoclinic phase [11]. Therefore the hopping integral between partners of the pair in this structure should be maxim al.

In Fig.1 we show the LDA and LDA+U spin-up band structure of  $V_2O_3$  in the energy range of the 12  $t_{2g}$  bands (4 V atom sper cell). C om paring these two pictures one can see that the LDA+U band structure calculated for U = 3eV and J= 0.8eV is essentially a rigid shift of the  $e_g$ band down in energy and  $a_{1g}$  up so that the form er is alm ost completely below the Ferm i energy and the later is above it. How ever, we note that as a result the m ixing between  $e_g$  and  $a_{1g}$  bands is suppressed. N evertheless, it is clear from Fig.1 that this m ixing does not com e from the hybridization between di erent orbitals of the atom s in the c-axis pair. This warns us already about the importance of the neighbours other than the partner in the pair.

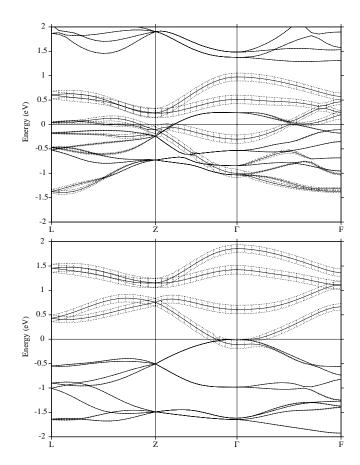


FIG.1: LDA (upper panel) and LDA+U (lower panel) spinup band structure of ferrom agnetic  $V_2O_3$  in the conundum structure with 2 form ula units per cell. The amount of  $a_{1g}$ character is indicated by the width of so-called fat bands (dotlines). We note that -Z is along the direction of the vertical pair (see Fig. 3.11 in [9] and Fig.1 in [18]). = (0,0,0); Z = (1/2,1/2,1/2); L = (0,1/2,0); F = (1/2,1/2,0). The zero of energy is at Ferm inenergy.

The LDA+U band structure, which yields a spin 1  $e_g e_g$  state, has the advantage that, as already m entioned, the empty  $a_{1g}$  band is practically separated from the full  $e_g$  band. Of course, this depends on the values of the parameters U and J used in the calculations. A c-cording to Solovyev et al. the calculated value of the screened parameter U and Hund's nule exchange J for V 3+ ion in LaVO<sub>3</sub> are 3eV and 0.93eV, respectively [12]. On the other hand, an empirical estim ate by M arel and Sawatzky, based on gas-phase multiplet splittings of the 3d series, shows that in the case of V 3d J is about 0.74eV [13]. In the present work we use J= 0.8eV as estim ated by Tanabe and Sugano for the free V 3+ ion [14, 15].

Before we discuss our results we note that, the width of the  $a_{1g}$  band reaches its maximum at , where it is about 2eV. One m ight believe that this width is mainly caused by the bonding-antibonding interaction between the vanadium pairs along the c-axis, and that the inter-

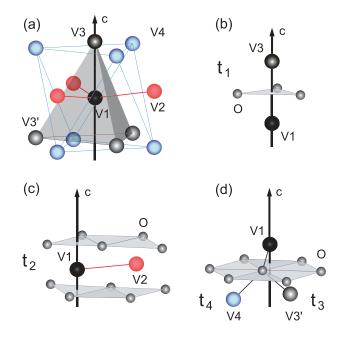


FIG.2: Vanadium neighbors in corundum structure which are taken into account in the tight-binding model (a). Denition of hopping parameters (b)  $t_1$  between the pair V1 and V3, (c)  $t_2$  between V1 and V2, (d)  $t_3$  between V1 and V3<sup>0</sup> and  $t_4$  between V1 and V4. The sm all spheres denote the oxygen ions to illustrate the importance of the bond angles.

action between pairs is weak. In the simplest such picture only two hopping parameters would be important: A large intra-pair hopping parameter, which should give the most of the bandwidth, and a smaller inter-pair hopping. This would result in a situation where the splitting of the  $a_{1g}$  band at the -point is primarily determined by the value of intra-pair hopping integral. How ever, one notices that the band splits into four almost equally separated levels.

To shed m ore light on this issue, we carry out a tightbinding model calculation where the hopping integrals to the rst  $(t_2)$ , second  $(t_2)$ , third  $(t_3)$  and fourth  $(t_4)$  nearest V neighbors are taken into account (Fig.2). Again, t<sub>1</sub> is the hopping integral between the atom s of the caxis pair. In Fig.3 (a) to (d) we dem onstrate how each of these param eters contribute in the dispersion of a<sub>1g</sub> band. N amely, switching on merely the hopping parameter  $t_1$ splits the atom ic  $a_{1q}$  level into two doubly degenerate at bands with energy di erence 2t. There is no dispersion because the atom s in-between the pairs in the structure are m issing. In fact, only because these atom s are m issing, does one see pairs at all. Now the main dispersion is caused by the hopping parameter t<sub>3</sub> which yields a maximal splitting of  $6t_3$  at the -point (the number of neighbors which an electron can hop to with t<sub>3</sub> is equal to 3). The hopping parameter  $t_4$  lifts the degeneracy of each of these doubly degenerate bands. Inclusion of to makes the band asymmetric with respect to the position of the

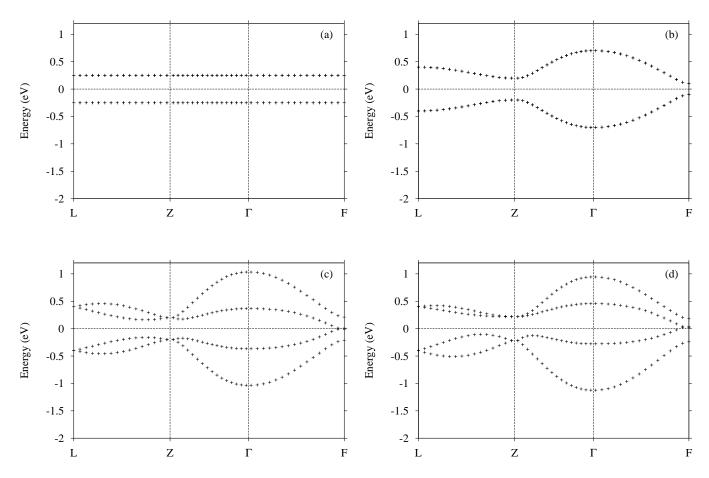


FIG. 3: Tight-binding  $a_{1g}$  bands. The zero of energy is at the center of the gap between the split bands. (a)  $t_1 = \{0.25eV, t_2=0, t_3=0, t_4=0.$  The splitting is 2  $t_1$  and there is no dispersion. (b)  $t_1 = \{0.25eV, t_2=0, t_3=\{0.15eV, t_4=0.$  Note that the large splitting at is dominated by  $t_3$  and not  $t_2$ . (c)  $t_1 = \{0.25eV, t_2=0, t_3=\{0.15eV, t_4=\{0.06eV.$  A small  $t_4$ ; but with 6 nearest neighbors, is su cient to cause the large splitting into 4 bands seen in the LDA + U band structure. (d)  $t_1 = \{0.25eV, t_2=0, t_3=\{0.15eV, t_4=\{0.06eV.$  A small  $t_4$ ; but with 6 nearest neighbors,  $t_3 = \{0.15eV, t_4=\{0.06eV.$  To obtain the very evident asymmetry between the upper and lower pairs of bands we need a small  $t_2$ . This is now close to the LDA + U band structure.

initial  $a_{1g}$  level. The nal result in Fig.3 (d) books very much like the LDA+U  $a_{1g}$  band. The parameters used are:  $t_1 = \{0.25eV, t_2 = \{0.03eV, t_3 = \{0.15eV, t_4 = \{0.06eV\}$ . A lthough  $t_1$  is indeed larger than other hopping integrals, its in uence on the bandwidth is not that large, because there is only one nearest neighbour, as compared to 3 for  $t_2$ , 3 for  $t_3$  and 6 for  $t_4$ .

It is in portant to note that these values for the hopping parameters are not unique. For example,  $t_1 = \{$ 0.5eV,  $t_2 = \{0.03eV$ ,  $t_3 = \{0.1eV \text{ and } t_4 = \{0.04eV \text{ would} \}$ also give a sm all splitting at the Z-point, and large one or L, as is shown in Fig.4. This has to do with the at symmetry of these points. At the Z-point, for instance, the splitting between the upper and low er com ponents of the  $a_{1g}$  band is  $2\beta t_3$   $t_1 j$  for  $t_2 = 0$ . Hence, for any given value of  $t_3$  there are always two values of  $t_1$ 3t3 <sub>z</sub> =2 which give exactly the same splitting. Note that  $t_4$  does not in uence the energies at Z. At the L-point, on the other hand, the splitting is determ ined primarily by the sum of  $t_1$  and  $t_3$ . Therefore, no set of parameters with

 $t_1$  greater than 0.5eV can reproduce the LDA+U band structure at this point (unless  $t_3$  and  $t_1$  have the opposite signs, which is "unphysical"). C om paring gures 1 and 4, one can easily see that the two sets of parameters, which give the same splitting at Z, will give di erent levels at F, and that only the set with  $t_1 = \{0.25 \text{ eV reproduces the accidental degeneray of the two m iddle levels in the LDA+U. How ever, to reproduce the LDA+U band in such detailm ay not be m eaningful as long as all hopping integrals beyond <math display="inline">t_4$  are neglected.

A lthough our tight-binding study has clearly demonstrated the role of the various hopping integrals for the dispersion of the  $a_{1g}$  band, and although we can ind param eters which it the LDA+U  $a_{g}$  band, it is difficult to select one set of hopping integrals because, to the accuracy expected for our model, dimentiates can do this. The most straightforward way to resolve this problem is to use the downfolding procedure of Andersen et. al. [16]. This procedure relies on keeping in the inst-principles NM TO band-structure calculation only the relevant de-

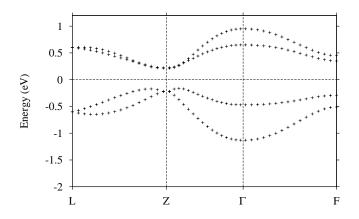


FIG .4: T ight-binding  $a_{1g}$  bands for  $t_1$  = {0.5eV ,  $t_2$  = {0.03eV ,  $t_3$  = {0.1eV and  $t_4$  = {0.04eV .

grees of freedom , in this case the  $a_{1\rm g}$  W annier-like orbitals whose LDA + U spin-up bands lie in the energy range from the Ferm i level to nearly 2 eV above, and integrating out the other degrees of freedom . This naturally takes into account re-norm alization e ects due to the integrated-out orbitals. Fourier transform of this few -orbital down folded and sym m etrically orthonorm alized NMTO Ham iltonian provides the hopping m atrix elem ents of the corresponding tight-binding Ham iltonian. This method provides a way of generating W annier-like functions and their singleparticle Ham iltonian without any tting procedure. The detailed discussion of such calculations for  $V_2O_3$ , as well as comparisons with Ham iltonians proposed previously, will be presented elsewhere [17]. Here we only mention a technical point speci c to the present application: Since the downfolding procedure takes place at a more basic level than where U is "added" to the LDA, we need to construct the potential which yields the spin-up LDA + U band structure. That potential we obtained from the LDA potentialby shifting its logarithm ic-derivative functions,  ${}'_{R}^{0}_{Im}$  (";s) =  ${}'_{R}_{Im}$  (";s); in energy so as to reproduce the spin-up LDA+U band structure.

From this NMTO downfolding calculation we obtained the follow ing hopping integrals:  $t_1 = \{0.30eV, t_2 = \{0.02eV, t_3 = \{0.11eV \text{ and } t_4 = \{0.05eV, which are close, although not identical to those used in Fig.3(d). As Fig.5(a) shows, the band structure obtained from these hopping integrals di ers a bit from that in Fig.3(d), and from the upper four LDA + U bands in Fig.1. The reason is sim ply that the downfolded band structure shown in Fig.5(b), obtained by downfolding to the the four <math>a_{1g}$  bands, cannot be reproduced completely with merely  $t_1; t_2; t_3;$  and  $t_4$ . Its Ham iltonian has also non-zero higher Fourier components, which is hardly suprising. The downfolding calculation thus con m s the gross values of the hopping integrals found by tight-binding tting to the rst 4 shells, but also points to the need for in-

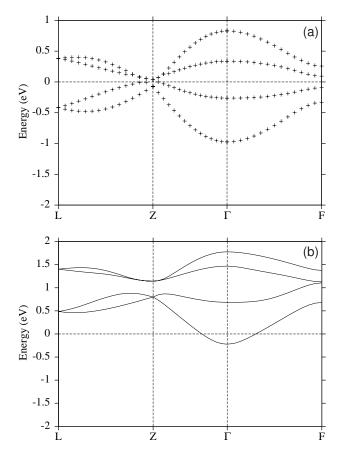


FIG.5: T ight-binding  $a_{1g}$  bands calculated with  $t_1 = \{0.3eV, t_2 = \{0.02eV, t_3 = \{0.11eV \text{ and } t_4 = \{0.05eV \text{ (upper panel) and those obtained from the downfolding procedure (lower panel). N ote that the zero of energy in the upper panel corresponds to the energy of atom ic <math>a_{1g}$  level but it is at Ferm i energy in the lower panel.

cluding longer ranged hoppings to reproduce the details.

O ne should keep in mind that the hopping integrals discussed above are for vanadium -centered W annier-like orbitals and thus di erent from the Slater-K oster hopping integrals for atom ic oxygen and vanadium orbitals obtained by M attheiss [18]. Follow ing H arrison one can show that the hopping integral between  $a_{1g}$  atom ic orbitals on the vanadium pair is about 0.8eV [19], whereas the one in which the oxygen degrees of freedom are integrated out is much less than that. This reduction is due to the anti-bonding character of the pd interaction.

We have thus demonstrated that, although the integral for hopping between the vertical pair is the largest hopping integral, it is not the single most in portant one for the  $a_{1g}$  bandwidth. This is so because the actual hopping integrals are not only determ ined by the direct V-V hoping but also evolve via interm ediate 0 2p orbitals. The simple picture where only the hopping parameter within the c-axis pair is important is not su cient to describe the  $a_{1g}$  band in V<sub>2</sub>O<sub>3</sub>. Our calculations show that the hopping integrals between second, third, and fourth nearest vanadium neighbors are equally important.

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